
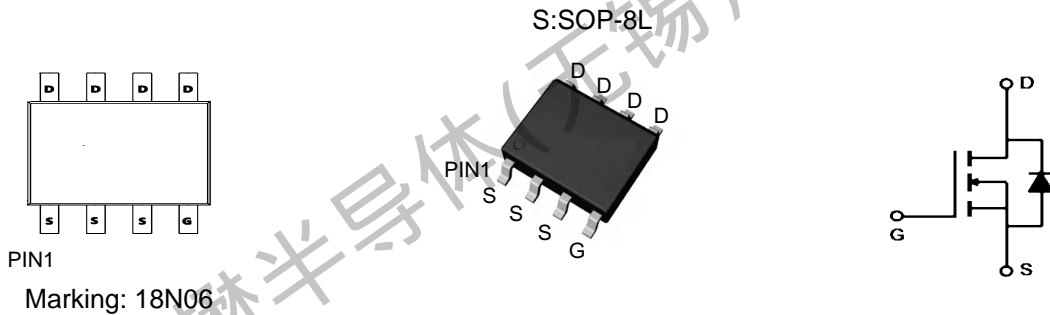


# TM18N06S

# N-Channel Enhancement Mosfet

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>General Features</b></p> <p><math>V_{DS} = 60V</math> <math>I_D = 18A</math></p> <p><math>R_{DS(ON)} = 15 m\Omega</math> (typ.) @ <math>V_{GS} = 10V</math></p> <p>100% UIS Tested 100% <math>R_g</math> Tested</p> 
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**Absolute Maximum Ratings** ( $T_A = 25^\circ C$  Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	18	A
$I_D @ T_A = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	12	A
$I_{DM}$	Pulsed Drain Current	39	A
$P_D$	Total Power Dissipation	2.1	W
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	80	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	---	25	$^\circ C/W$



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Electrical Characteristics: ( $T_A=25^\circ\text{C}$  unless otherwise noted)

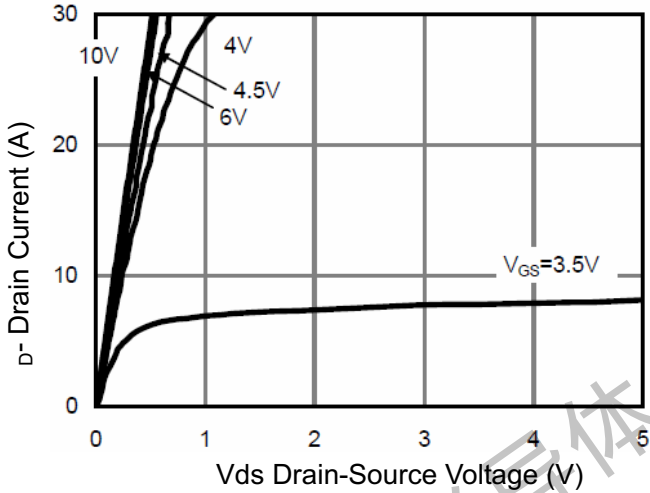
Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu A$	60	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=60V, T_C=25^\circ\text{C}$	---	---	1	$\mu A$
		$V_{GS}=0V, V_{DS}=60V, T_C=125^\circ\text{C}$	---	---	100	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu A$	1.0	2.0	3.0	V
$R_{DS(ON)}$	Drain-Source On Resistance	$V_{GS}=10V, I_D=8A$	---	15	18	m $\Omega$
		$V_{GS}=4.5V, I_D=4A$	---	19	25	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=30V, V_{GS}=0V, f=1\text{MHz}$	---	1688	---	pF
$C_{oss}$	Output Capacitance		---	112	---	
$C_{rss}$	Reverse Transfer Capacitance		---	91	---	
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, I_D=20A$ $R_G=3\ \Omega, V_{GS}=10V$	---	6.7	---	ns
$t_r$	Rise Time		---	3.3	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	21	---	ns
$t_f$	Fall Time		---	6.2	---	ns
$Q_g$	Total Gate Charge	$V_{GS}=10V, V_{DS}=30V,$ $I_D=20A$	---	39	---	nC
$Q_{gs}$	Gate-Source Charge		---	7.7	---	nC
$Q_{gd}$	Gate-Drain "Miller" Charge		---	8.3	---	nC
<b>Drain-Source Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=20A, T_J=25^\circ\text{C}$	---	---	1.2	V
$I_S$	Source drain current(Body Diode)	$V_D=V_G=0V$	---	---	18	A
$T_{rr}$	Reverse Recovery Time	$I_F=20A, di_F/dt=100A/\mu s$	---	29	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	21	---	nC



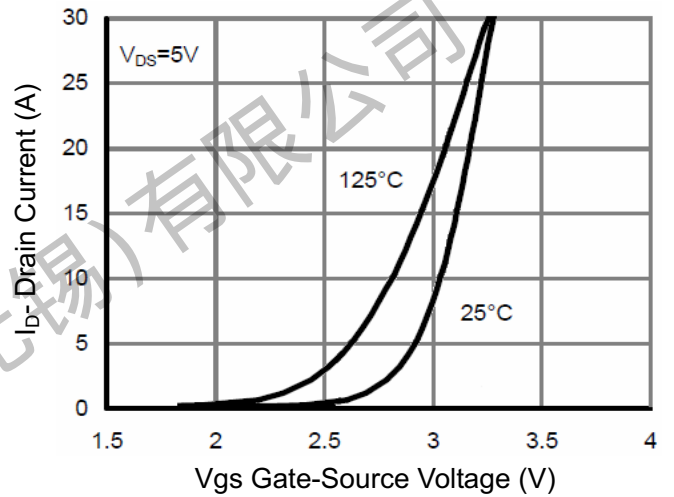
**TM18N06S**

**N-Channel Enhancement Mosfet**

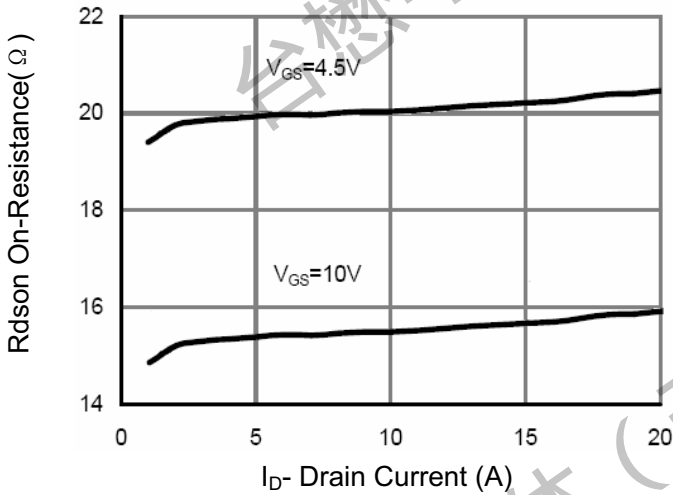
Typical Characteristics



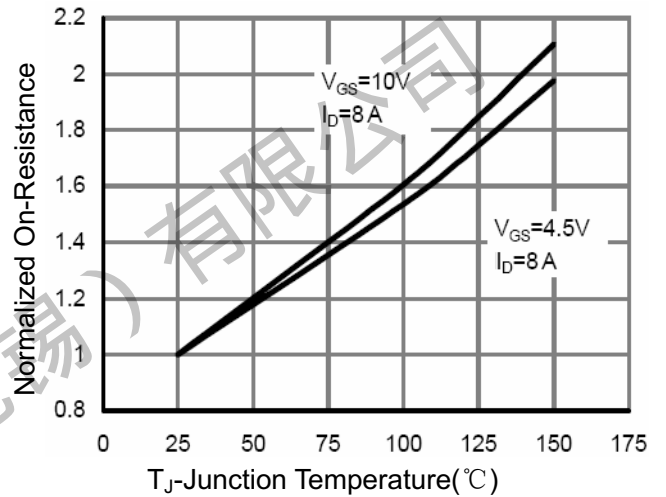
**Figure 1 Output Characteristics**



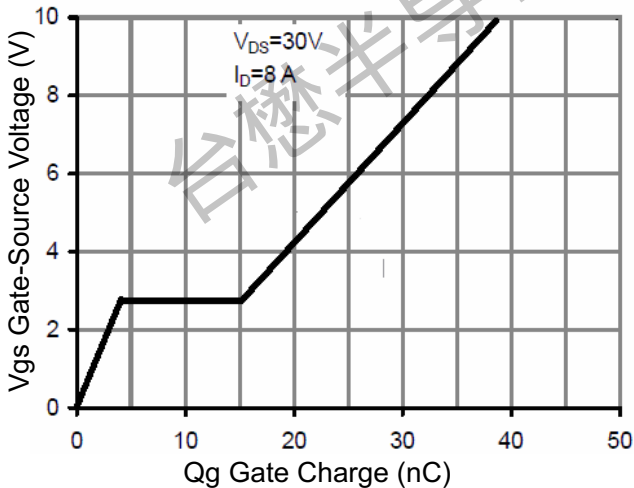
**Figure 2 Transfer Characteristics**



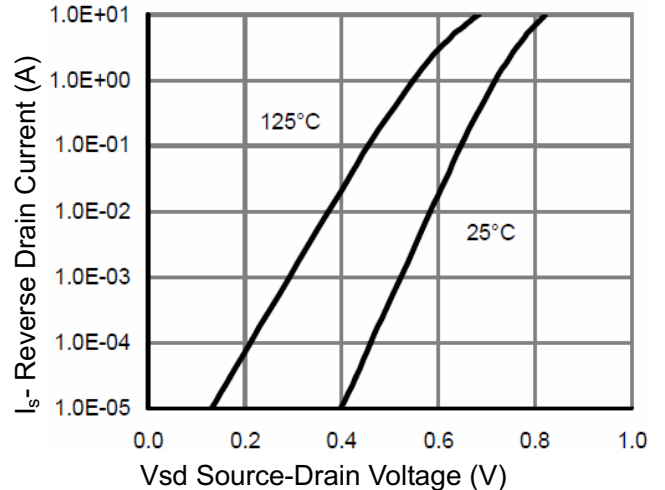
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**



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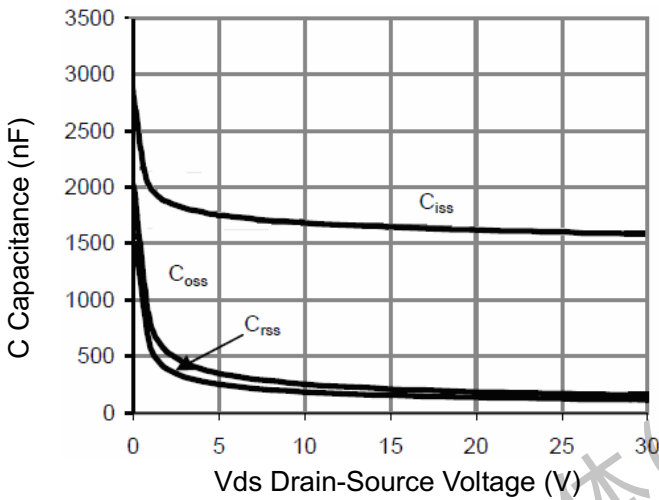


Figure 7 Capacitance vs Vds

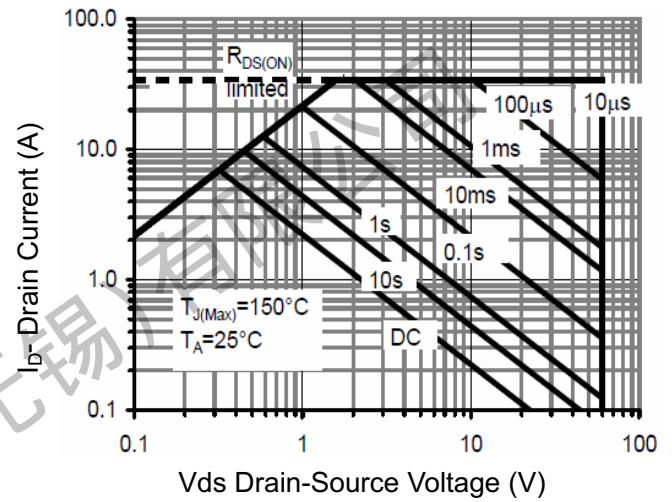


Figure 8 Safe Operation Area

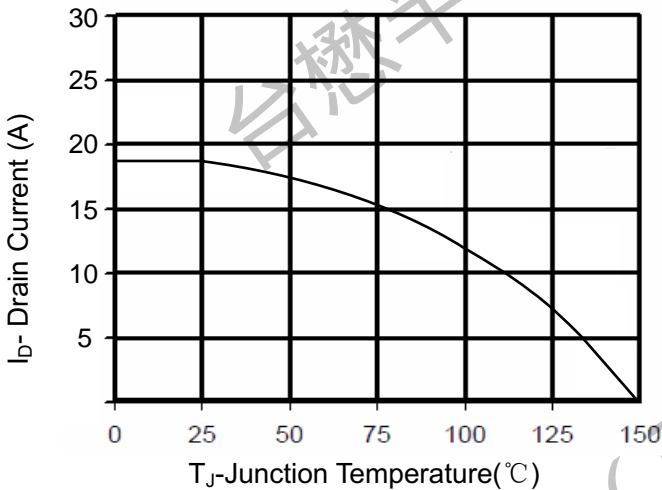


Figure 9 Current De-rating

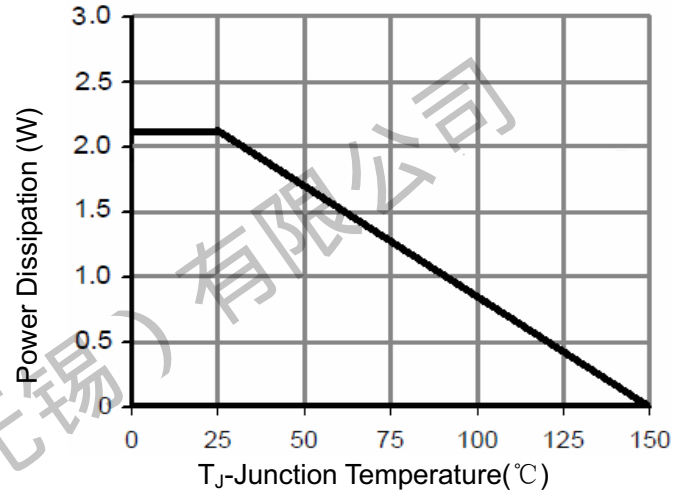


Figure 10 Power De-rating

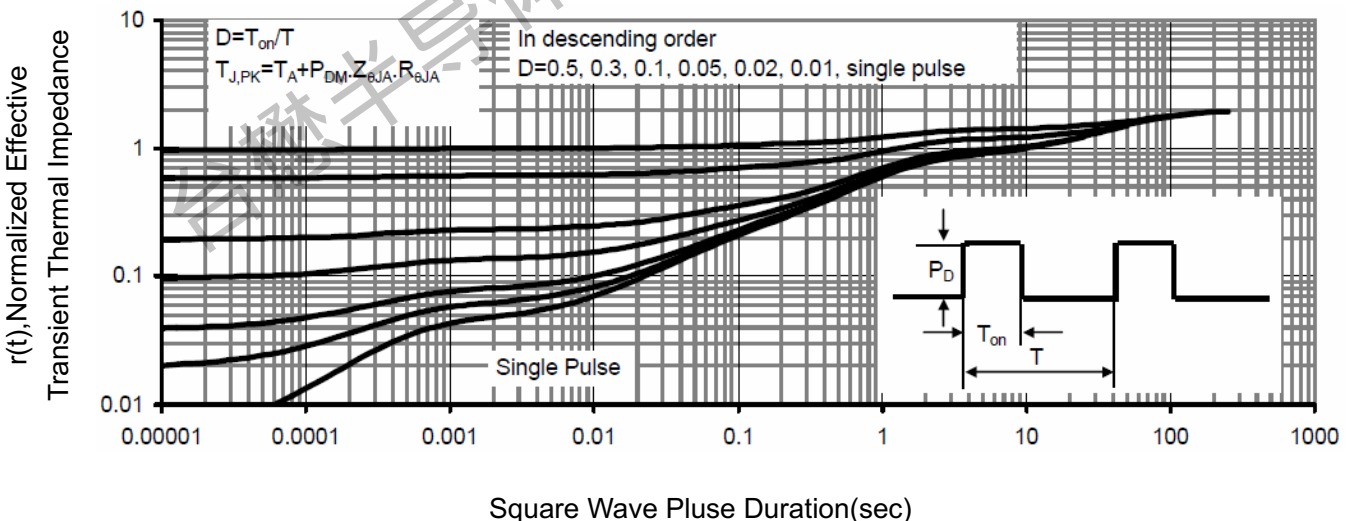


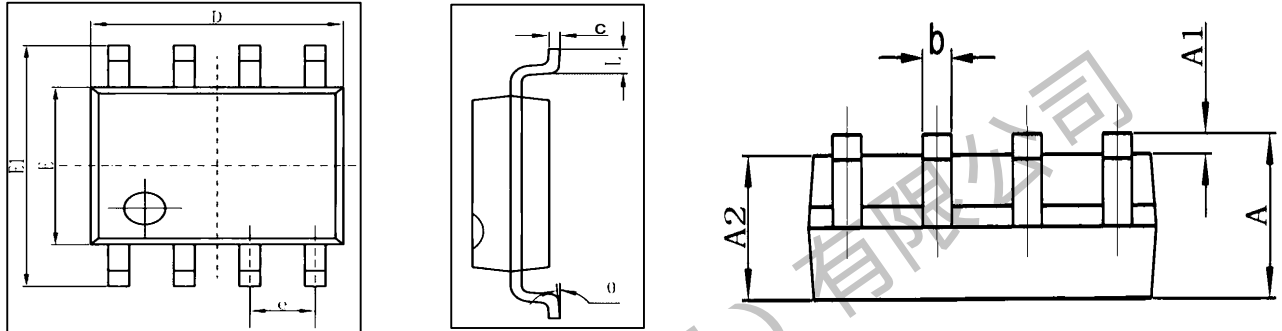
Figure 11 Normalized Maximum Transient Thermal Impedance



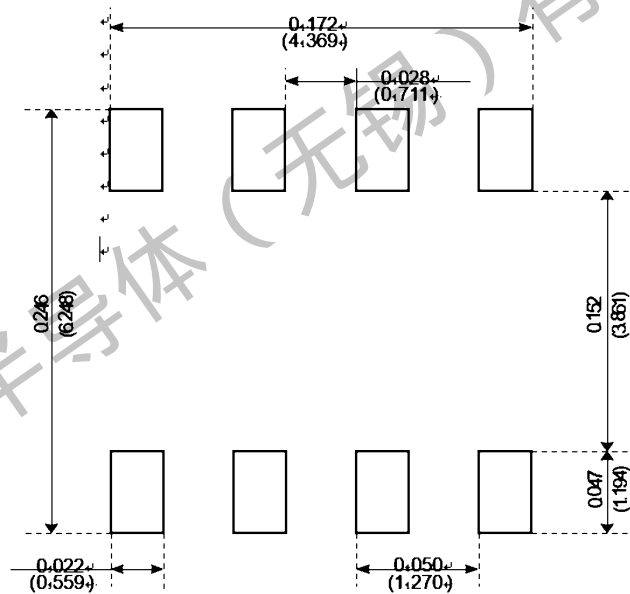
**TM18N06S**

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**Package Mechanical Data:SOP-8L**



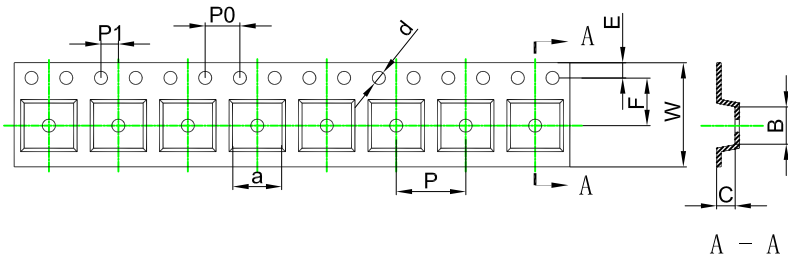
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



**TM18N06S**

**N-Channel Enhancement Mosfet**

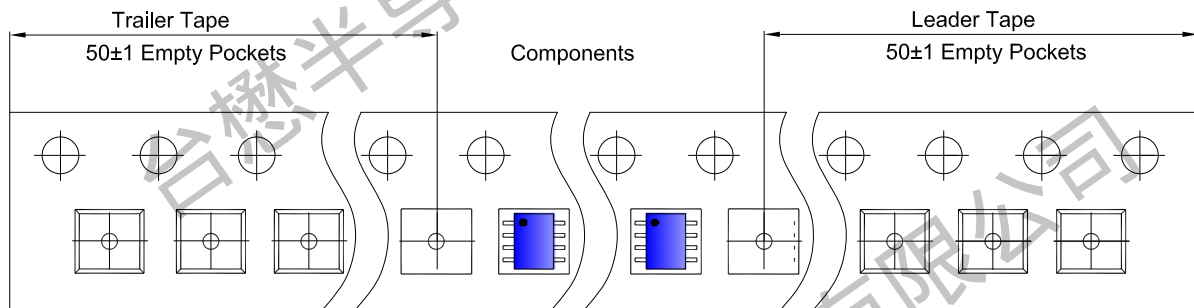
**SOP-8L Embossed Carrier Tape**



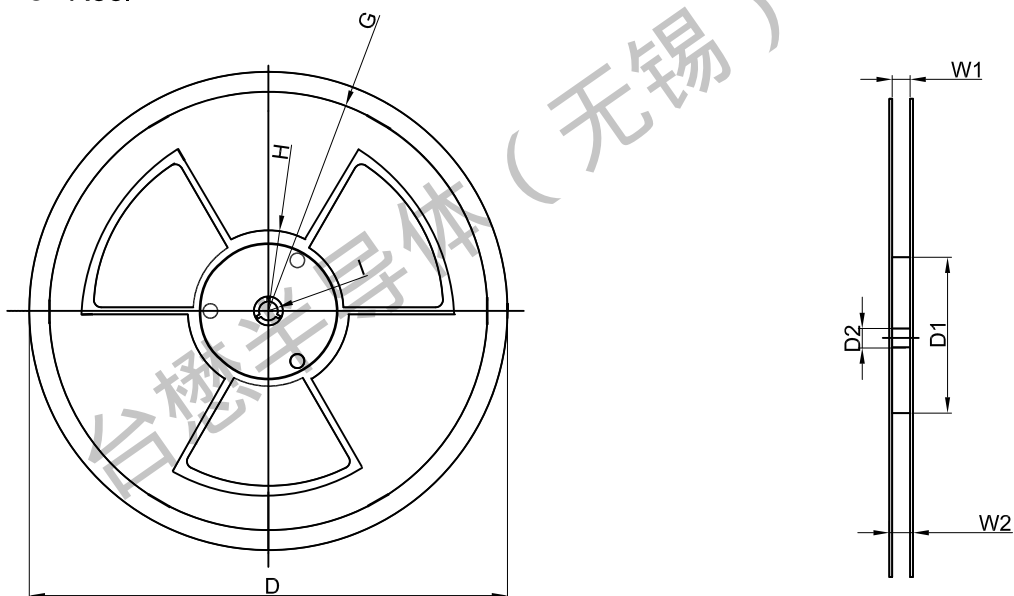
**Packaging Description:**  
SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).  
**ALL DIM IN mm**

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
SOP-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

**SOP-8L Tape Leader and Trailer**



**SOP-8L Reel**



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3,000 pcs	13 inch	6,000 pcs	370×355×52	48,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.05.16	23.05	Original	